

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. – 19. (Cancelled)

20. (Currently Amended) A wiring tape for a semiconductor device, which comprises a wiring layer comprising an insulating layer and a wiring on the insulating layer, one end of the wiring being connected to terminals on ~~the~~a semiconductor chip and the other end of the wiring being connected to external terminals for connecting to a package substrate; and a three-layered buffer layer bonded to the wiring-formed side of the wiring layer, the buffer layer comprising a structure having interconnected foams or a three-dimensional reticular structure, an adhesive layer provided on the semiconductor chip-facing side of the structure having interconnected foams or the three-dimensional reticular structure, directed to bonding to the semiconductor chip and another adhesive layer provided on the other side of the structure, directed to bonding to the wiring layer to relax thermal stress generated between the semiconductor chip and the package substrate during heating.

21. (Currently Amended) ~~An adhesive~~A wiring tape according to Claim 20, wherein a thickness ~~ratio~~ratio of the structure having interconnected foams or the three-dimensional reticular structure to total buffer layer thickness is at least 0.2 to

reduce the likelihood of failure of the semiconductor device during heating performed in a reflow operation used in manufacturing the semiconductor device.

22. (Currently Amended) ~~An adhesive~~ A wiring tape according to Claim 20, wherein the buffer layer is ~~composed~~ comprised of a laminate prepared by pasting both sides of the structure having interconnected foams or the three-dimensional reticular structure with the adhesive layers, respectively.

23. (Original) A wiring tape according to Claim 20, wherein the buffer layer is composed of a laminate prepared by pasting both sides of the structure having interconnected foams with adhesive layers each comprising a structure having interconnected foams whose pores are filled with an adhesive, respectively.

24. (New) A wiring tape for a semiconductor device, which comprises a wiring layer comprising an insulating layer and a wiring on the insulating layer, one end of the wiring being connected to terminals on a semiconductor chip and the other end of the wiring being connected to external terminals for connecting to a package substrate; and means for relaxing thermal stress generated between the semiconductor chip and the package substrate and for releasing steam pressure generated during heating in a reflow operation used in forming a package, including the wiring tape and the semiconductor device, to outside of the package, said means comprising:

a three-layered buffer layer bonded to the wiring-formed side of the wiring layer, the buffer layer comprising a structure having interconnected foams or a three-

dimensional reticular structure, an adhesive layer provided on the semiconductor chip-facing side of the structure having interconnected foams or the three-dimensional reticular structure, directed to bonding to the semiconductor chip and another adhesive layer provided on the other side of the structure, directed to bonding to the wiring layer.

25. (New) A wiring tape according to Claim 24, wherein a thickness ratio of the structure having interconnected foams of the three-dimensional reticular structure to total buffer layer thickness is at least 0.2 to reduce the likelihood of failure of the semiconductor device during heating performed in a reflow operation used in manufacturing the semiconductor device.

26. (New) A wiring tape according to Claim 24, wherein the buffer layer is comprised of a laminate prepared by pasting both sides of the structure having interconnected foams or the three-dimensional reticular structure with the adhesive layers, respectively.